## Atty Docket No. Application No.: UNTYP015 10/612,733 Information Disclosure Statement By Applicant (Use Several Sheets if Necessary) Atty Docket No. Application No.: UNTYP015 10/612,733 Applicant: Rinerson et al. Filing Date Group July 1, 2003 2818 2824

## U.S. Patent Documents

Examiner						Sub-	Filing
Initial	No.	Patent No.	Date	Patentee	Class	class	Date
سو	A	6,204,139	2001-03-20	Liu et al.			
	В	5,920,500	1999-07-06	Tehrani et al.			
	C	6,545,891	2003-04-08	Tringali et al.			<u> </u>
	D	6,504,753	2003-01-07	Scheuerlein et al.			
	E	6,483,736	2002-11-19	Johnson et al.			
	F	6,385,074	2002-05-07	Johnson et al.			
	G	6,351,406	2002-02-26	Johnson et al.			
	H	6,185,122	2001-02-06	Johnson et al.			
	I	6,034,882	2000-03-07	Johnson et al.			
	J	5,835,396	1998-11-10	Zhang			
ou	K	4,442,507	1994-04-10	Roesner			

**U.S. Published Patent Applications** 

Examiner		Document	Publication	Inventor
Initial	No.	No.	Date	
<b>.</b> 9્ય	J	2002/0000597 A1	01/03/02	Okazawa
<b>૭</b> ૫	K	2001/0023992 A1	09/27/01	Doll

## Other Documents

		Other Documents			
Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication			
Qu	L	Beck, A. et al., "Reproducible switching effect in thin oxide films for memory applications", Applied Physics Letters, Vol. 77, No. 1, 3 July 2000,139-141.			
ger	M	Rossel, C. et al., "Electrical current distribution across a metal-insulator-metal structure during bistable switching", Journal of Applied Physics, Vol. 90, No. 6, 15 September 2001, 2892-2898.			
gu	N	Watanabe, Y. et al., "Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO <sub>3</sub> single crystals", Applied Physics Letters, Vol. 78, No. 23, 4 June 2001, 3738-3740.			
Examiner Vu le		Date Considered 8/30/05			

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

The Filing Date

(Use Several Sheets if Necessary)

Atty Docket No. Application No.:

10/612,733

Applicant:

Rinerson et al.

Filing Date

July 1, 2003

Application No.:

10/612,733

Application No.:

10/612,733

Applicant:

Rinerson et al.

Filing Date

July 1, 2003

## Other Documents

Examiner				
Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication		
gu	A <sub>.</sub>	Liu, S.Q., et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", Applied Physics Letters, Vol. 76, No. 19, 8 May 2000, 2749-2651.		
مىق	В	Liu, S.Q., et al., "A New Concept For Non-Volatile Memory: Electric-Pulse Induced Reversible Resistance Change Effect In Magnetoresistive Films", Space Vacuum Epitaxy Center, University of Huston, Huston TX, 7 Pages.		
		·		
Examiner	V	u le Date Considered 8/30/05		

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.